Kohei Hamaya

List of Publications by Year
in descending order

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216 papers	3,863 citations	109321 35 h-index	189892 50 g-index
219 all docs	219 docs citations	219 times ranked	1723 citing authors

#	Article	IF	Citations
1	Electrical injection and detection of spin-polarized electrons in silicon through an Fe3Si/Si Schottky tunnel barrier. Applied Physics Letters, 2009, 94, 182105.	3.3	119
2	Ferromagnetism and Electronic Structures of Nonstoichiometric Heusler-Alloy<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Fe</mml:mi><mml:mrow><mml:mn>3</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math> Grown on Ge(111). Physical Review Letters, 2009, 102, 137204.	7.8	94
3	Epitaxial ferromagnetic Fe3Siâ•Si(111) structures with high-quality heterointerfaces. Applied Physics Letters, 2008, 93, .	3.3	86
4	Room-temperature generation of giant pure spin currents using epitaxial Co2FeSi spin injectors. NPG Asia Materials, 2012, 4, e9-e9.	7.9	86
5	Spin transport through a single self-assembled InAs quantum dot with ferromagnetic leads. Applied Physics Letters, 2007, 90, 053108.	3.3	83
6	Estimation of the spin polarization for Heusler-compound thin films by means of nonlocal spin-valve measurements: Comparison of Co<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>FeSi and Fe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>Si. Physical Review B, 2012, 85, .	3.2	81
7	Electric-field control of tunneling magnetoresistance effect in a Niâ•InAsâ•Ni quantum-dot spin valve. Applied Physics Letters, 2007, 91, .	3.3	75
8	Effect of atomically controlled interfaces on Fermi-level pinning at metal/Ge interfaces. Applied Physics Letters, 2010, 96, .	3.3	75
9	Kondo effect in a semiconductor quantum dot coupled to ferromagnetic electrodes. Applied Physics Letters, 2007, 91, .	3.3	70
10	Magnetotransport study of temperature dependent magnetic anisotropy in a (Ga,Mn)As epilayer. Journal of Applied Physics, 2003, 94, 7657.	2.5	69
11	High carrier mobility in orientation-controlled large-grain (â‰¥50â€‰Î¼m) Ge directly formed on flexible plastic by nucleation-controlled gold-induced-crystallization. Applied Physics Letters, 2014, 104, .	3.3	66
12	Significant growth-temperature dependence of ferromagnetic properties for Co2FeSi/Si(111) prepared by low-temperature molecular beam epitaxy. Applied Physics Letters, 2010, 96, .	3.3	65
13	Greatly enhanced generation efficiency of pure spin currents in Ge using Heusler compound Co₂FeSi electrodes. Applied Physics Express, 2014, 7, 033002.	2.4	65
14	Spin accumulation created electrically in an n-type germanium channel using Schottky tunnel contacts. Journal of Applied Physics, 2012, 111, .	2.5	62
15	Oscillatory changes in the tunneling magnetoresistance effect in semiconductor quantum-dot spin valves. Physical Review B, 2008, 77, .	3.2	59
16	Electric-field control of spin accumulation signals in silicon at room temperature. Applied Physics Letters, 2011, 99, 132511.	3.3	56
17	Spin Transport and Relaxation up to 250Â K in Heavily Doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>n</mml:mi></mml:math> -Type Ge Detected Using <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>FeSi/Ge Ferromagnetic Schottky Contacts. Physical Review Applied, 2017, 7, .	3.8	52
18	Local structural ordering in low-temperature-grown epitaxial Fe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>3</mml:mn><mml:mo>+</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:mrow></mml:math>Si films on Si(111) substrates. Physical Review B, 2012, 85, .	3.2	51

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19	Room-temperature structural ordering of a Heusler compound Fe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>Si. Physical Review B, 2012, 86, .	3.2	48
20	Spin transport and relaxation in germanium. Journal Physics D: Applied Physics, 2018, 51, 393001.	2.8	48
21	Giant Spin Accumulation in Silicon Nonlocal Spin-Transport Devices. Physical Review Applied, 2017, 8, .	3.8	47
22	Effect of the interface resistance of CoFe/MgO contacts on spin accumulation in silicon. Applied Physics Letters, 2012, 100, .	3.3	46
23	Bias current dependence of spin accumulation signals in a silicon channel detected by a Schottky tunnel contact. Applied Physics Letters, 2011, 99, .	3.3	45
24	Electrical polarization of nuclear spins in a breakdown regime of quantum Hall effect. Applied Physics Letters, 2007, 90, 022102.	3.3	44
25	Highly ordered Co2FeSi Heusler alloys grown on Ge(111) by low-temperature molecular beam epitaxy. Journal of Applied Physics, 2010, 107, .	2.5	44
26	Electrical properties of pseudo-single-crystalline germanium thin-film-transistors fabricated on glass substrates. Applied Physics Letters, 2015, 107, .	3.3	44
27	A pseudo-single-crystalline germanium film for flexible electronics. Applied Physics Letters, 2015, 106, .	3.3	44
28	Comparison of Nonlocal and Local Magnetoresistance Signals in Laterally Fabricated Fe₃Si/Si Spin-Valve Devices. Applied Physics Express, 2010, 3, 093001.	2.4	42
29	Mixed Magnetic Phases in(Ga,Mn)AsEpilayers. Physical Review Letters, 2005, 94, 147203.	7.8	40
30	Low-temperature molecular beam epitaxy of a ferromagnetic full-Heusler alloy Fe2MnSi on Ge(111). Applied Physics Letters, 2008, 93, 112108.	3.3	39
31	Spin-Related Current Suppression in a Semiconductor Quantum Dot Spin-Diode Structure. Physical Review Letters, 2009, 102, 236806.	7.8	39
32	Dynamical Spin Injection into p-Type Germanium at Room Temperature. Applied Physics Express, 2013, 6, 023001.	2.4	39
33	Magnetic properties of epitaxially grown Fe3Si/Ge(111) layers with atomically flat heterointerfaces. Journal of Applied Physics, 2009, 105, .	2.5	38
34	Spin relaxation through lateral spin transport in heavily doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math> -type silicon. Physical Review B, 2017, 95, .	3.2	38
35	Atomically Controlled Epitaxial Growth of Single-Crystalline Germanium Films on a Metallic Silicide. Crystal Growth and Design, 2012, 12, 4703-4707.	3.0	37
36	Structural and electrical properties of Ge(111) films grown on Si(111) substrates and application to Ge(111)-on-Insulator. Thin Solid Films, 2016, 613, 24-28.	1.8	36

#	Article	IF	Citations
37	Sourceâ€“Drain Engineering Using Atomically Controlled Heterojunctions for Next-Generation SiGe Transistor Applications. Japanese Journal of Applied Physics, 2011, 50, 010101.	1.5	35
38	Qualitative study of temperature-dependent spin signals in n-Ge-based lateral devices with Fe3Si/n+-Ge Schottky-tunnel contacts. Journal of Applied Physics, 2013, 113, .	2.5	34
39	Improvement of magnetic and structural stabilities in high-quality Co2FeSi1â^'xAlx/Si heterointerfaces. Applied Physics Letters, 2014, 105, .	3.3	34
40	Magnetic anisotropy switching in(Ga,Mn)Aswith increasing hole concentration. Physical Review B, 2006, 74, .	3.2	33
41	Giant enhancement of spin pumping efficiency using Fe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>Si ferromagnet. Physical Review B, 2013, 88, .	3.2	33
42	Mechanism of Fermi level pinning at metal/germanium interfaces. Physical Review B, 2011, 84, .	3.2	32
43	Spin injection through energy-band symmetry matching with high spin polarization in atomically controlled ferromagnet/ferromagnet/semiconductor structures. NPG Asia Materials, 2020, 12, .	7.9	32
44	Temperature evolution of spin accumulation detected electrically in a nondegenerated silicon channel. Physical Review B, 2012, 85, .	3.2	31
45	Room-temperature spin transport in n-Ge probed by four-terminal nonlocal measurements. Applied Physics Express, 2017, 10, 093001.	2.4	31
46	Temperature-independent spin relaxation in heavily doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math> -type germanium. Physical Review B, 2016, 94, .	3.2	30
47	Ultrashallow Ohmic contacts for n-type Ge by Sb Î´-doping. Applied Physics Letters, 2010, 97, .	3.3	29
48	High-quality epitaxial CoFe/Si(111) heterostructures fabricated by low-temperature molecular beam epitaxy. Applied Physics Letters, 2010, 97, .	3.3	28
49	Local magnetoresistance through Si and its bias voltage dependence in ferromagnet/MgO/silicon-on-insulator lateral spin valves. Journal of Applied Physics, 2014, 115, .	2.5	27
50	Contribution of Shape Anisotropy to the Magnetic Configuration of (Ga, Mn)As. Japanese Journal of Applied Physics, 2004, 43, L306-L308.	1.5	25
51	Low-temperature grown quaternary Heusler-compound Co₂Mn_{1â^'x}Fe_xSi films on Ge(111). Journal of Applied Physics, 2011, 109, 07B113.	2.5	25
52	Formation of Tensilely Strained Germanium-on-Insulator. Applied Physics Express, 2012, 5, 015701.	2.4	25
53	Electrical properties of pseudo-single-crystalline Ge films grown by Au-induced layer exchange crystallization at 250â€‰Â°C. Journal of Applied Physics, 2018, 123, 215704.	2.5	24
54	Spin transport in p-Ge through a vertically stacked Ge/Fe3Si junction. Applied Physics Letters, 2016, 109, .	3.3	23

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55	Current-Induced Magnetization Reversal in a (Ga,Mn)As-Based Magnetic Tunnel Junction. Japanese Journal of Applied Physics, 2004, 43, L825-L827.	1.5	22
56	An ultra-thin buffer layer for Ge epitaxial layers on Si. Applied Physics Letters, 2013, 102, .	3.3	22
57	Large impact of impurity concentration on spin transport in degenerate n -Ge. Physical Review B, 2017, 95, .	3.2	22
58	Spin-Based MOSFETs for Logic and Memory Applications and Spin Accumulation Signals in CoFe/Tunnel Barrier/SOI Devices. IEEE Transactions on Magnetics, 2012, 48, 2739-2745.	2.1	21
59	Maximum magnitude in bias-dependent spin accumulation signals of CoFe/MgO/Si on insulator devices. Journal of Applied Physics, 2013, 114, .	2.5	21
60	Spin transport and accumulation in n+-Si using Heusler compound Co2FeSi/MgO tunnel contacts. Applied Physics Letters, 2015, 107, .	3.3	21
61	Anomalous Hall conductivity and electronic structures of Si-substituted <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Mn</mml:mi><mml:mn>2</mml:mn></ml epitaxial films. Physical Review B, 2018, 97, .	3.2	21
62	Nonlinear Electrical Spin Conversion in a Biased Ferromagnetic Tunnel Contact. Physical Review Applied, 2018, 10, .	3.8	21
63	Room-temperature detection of spin accumulation in silicon across Schottky tunnel barriers using a metalâ€“oxideâ€“semiconductor field effect transistor structure (invited). Journal of Applied Physics, 2013, 113, .	2.5	20
64	A crystalline germanium flexible thin-film transistor. Applied Physics Letters, 2017, 111, .	3.3	20
65	Epitaxial growth of a full-Heusler alloy Co2FeSi on silicon by low-temperature molecular beam epitaxy. Thin Solid Films, 2010, 518, S278-S280.	1.8	19
66	Effect of Addition of Al to Single-Crystalline CoFe Electrodes on Nonlocal Spin Signals in Lateral Spin-Valve Devices. Applied Physics Express, 2012, 5, 063004.	2.4	18
67	Large anisotropy of Gilbert damping constant in L2₁-ordered Co₂FeSi film. Applied Physics Express, 2014, 7, 123001.	2.4	18
68	High-quality Co2FeSi0.5Al0.5/Si heterostructures for spin injection in silicon spintronic devices. Thin Solid Films, 2014, 557, 390-393.	1.8	18
69	Realisation of magnetically and atomically abrupt half-metal/semiconductor interface: Co2FeSi0.5Al0.5/Ge(111). Scientific Reports, 2016, 6, 37282.	3.3	18
70	Pure spin current transport in a SiGe alloy. Applied Physics Express, 2018, 11, 053006.	2.4	18
71	Electrical coherent control of nuclear spins in a breakdown regime of quantum Hall effect. Applied Physics Letters, 2007, 91, .	3.3	17
72	All-epitaxial Co2FeSi/Ge/Co2FeSi trilayers fabricated by Sn-induced low-temperature epitaxy. Journal of Applied Physics, 2016, 119, .	2.5	17

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73	Direct evidence for suppression of the Kondo effect due to pure spin current. Physical Review B, 2016, 94, .	3.2	17
74	Low-temperature growth of fully epitaxial CoFe/Ge/Fe₃Si layers on Si for vertical-type semiconductor spintronic devices. Semiconductor Science and Technology, 2017, 32, 094005.	2.0	17
75	Magnetic and transport properties of equiatomic quaternary Heusler CoFeVSi epitaxial films. Physical Review Materials, 2018, 2, .	2.4	17
76	Sourceâ€“Drain Engineering Using Atomically Controlled Heterojunctions for Next-Generation SiGe Transistor Applications. Japanese Journal of Applied Physics, 2011, 50, 010101.	1.5	17
77	Room-temperature two-terminal magnetoresistance ratio reaching 0.1% in semiconductor-based lateral devices with L21-ordered Co2MnSi. Applied Physics Letters, 2021, 118, .	3.3	16
78	Electrical detection of spin accumulation and relaxation in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>p</mml:mi></mml:math> -type germanium. Physical Review Materials, 2017, 1, .	2.4	16
79	The role of chemical structure on the magnetic and electronic properties of Co2FeAl0.5Si0.5/Si(111) interface. Applied Physics Letters, 2016, 108, .	3.3	15
80	Spin injection into multilayer graphene from highly spin-polarized Co2FeSi Heusler alloy. Applied Physics Express, 2016, 9, 063006.	2.4	15
81	Correlation between spin transport signal and Heusler/semiconductor interface quality in lateral spin-valve devices. Physical Review B, 2018, 98, .	3.2	15
82	Significant reduction in the thermal conductivity of Si-substituted <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Fe</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> epilayers. Physical Review B, 2019, 99, .	3.2	15
83	Positive linear magnetoresistance effect in disordered <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>L</mml:mi><mml:msub><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> -type <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow><mml:mi>Mn</mml:mi></mml:mrow><mml:mn>2</mml:mn></mml:msub></mml:math> epitaxial films. Physical Review B, 2021, 103, .	3.2	15
84	Room-temperature sign reversed spin accumulation signals in silicon-based devices using an atomically smooth Fe3Si/Si(111) contact. Journal of Applied Physics, 2013, 113, .	2.5	14
85	Effect of Co-Fe substitution on room-temperature spin polarization in Co<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>3</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>Fe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>Si Heusler-compound films. Physical Review B, 2013, 88, .	3.2	14
86	Lateral spin valves with two-different Heusler-alloy electrodes on the same platform. Applied Physics Letters, 2013, 103, .	3.3	14
87	Molecular Beam Epitaxy of Co₂MnSi Films on Group-IV Semiconductors. Japanese Journal of Applied Physics, 2013, 52, 04CM06.	1.5	14
88	Finely Controlled Approaches to Formation of Heusler-Alloy/Semiconductor Heterostructures for Spintronics. Materials Transactions, 2016, 57, 760-766.	1.2	14
89	Nonmonotonic bias dependence of local spin accumulation signals in ferromagnet/semiconductor lateral spin-valve devices. Physical Review B, 2019, 100, .	3.2	14
90	Reliable reduction of Fermi-level pinning at atomically matched metal/Ge interfaces by sulfur treatment. Applied Physics Letters, 2014, 104, 172109.	3.3	13

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91	Suppression of Donor-Driven Spin Relaxation in Strained <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi>Si</mml:mi><mml:mrow><mml:mn>0.1</mml:mn></mml:mrow></mml:msub><mml:msub><mml: Physical Review Applied, 2020, 13, .	3.8	13
92	Giant converse magnetoelectric effect in a multiferroic heterostructure with polycrystalline Co2FeSi. NPG Asia Materials, 2022, 14, .	7.9	13
93	Semiconductor spintronics with Co2-Heusler compounds. MRS Bulletin, 2022, 47, 584-592.	3.5	13
94	Selective dry etching of manganite thin films for high sensitive magnetoresistive sensors. Journal of Magnetism and Magnetic Materials, 2001, 235, 223-226.	2.3	12
95	Significant Change in In-Plane Magnetic Anisotropy of (Ga,Mn)As Epilayer Induced by Low-Temperature Annealing. Japanese Journal of Applied Physics, 2004, 43, L904-L906.	1.5	12
96	Dynamic relaxation of magnetic clusters in a ferromagnetic(Ga,Mn)Asepilayer. Physical Review B, 2006, 73, .	3.2	12
97	Knight shift detection using gate-induced decoupling of the hyperfine interaction in quantum Hall edge channels. Applied Physics Letters, 2006, 89, 062108.	3.3	12
98	Influence of Al co-deposition on the crystal growth of Co-based Heusler-compound thin films on Si(111). Thin Solid Films, 2012, 520, 3419-3422.	1.8	12
99	Spin-related thermoelectric conversion in lateral spin-valve devices with single-crystalline Co₂FeSi electrodes. Applied Physics Express, 2015, 8, 043003.	2.4	12
100	Low thermal conductivity of thermoelectric Fe₂VAl films. Applied Physics Express, 2017, 10, 115802.	2.4	12
101	Control of electrical properties in Heusler-alloy/Ge Schottky tunnel contacts by using phosphorous Î´-doping with Si-layer insertion. Materials Science in Semiconductor Processing, 2017, 70, 83-85.	4.0	12
102	Observation of local magnetoresistance signals in a SiGe-based lateral spin-valve device. Semiconductor Science and Technology, 2018, 33, 114009.	2.0	12
103	Quantification of Spin Drift in Devices with a Heavily Doped <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Si</mml:mi></mml:math> Channel. Physical Review Applied, 2019, 11, .	3.8	12
104	Thermoelectric properties of single-phase full-Heusler alloy Fe2TiSi films with D3-type disordering. Journal of Applied Physics, 2020, 127, .	2.5	12
105	Tunneling magnetoresistance effect in a few-electron quantum-dot spin valve. Applied Physics Letters, 2008, 93, 222107.	3.3	11
106	Molecular beam epitaxial growth of ferromagnetic Heusler alloys for group-IV semiconductor spintronic devices. Thin Solid Films, 2010, 518, S273-S277.	1.8	11
107	Correlation between amplitude of spin accumulation signals investigated by Hanle effect measurement and effective junction barrier height in CoFe/MgO/n+-Si junctions. Journal of Applied Physics, 2015, 117, .	2.5	11
108	Local Magnetoresistance at Room Temperature in Si <inline-formula> <tex-math notation="LaTeX">$langle100angle$ </tex-math> </inline-formula> Devices. IEEE Transactions on Magnetics, 2018, 54, 1-4.	2.1	11

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109	Room-temperature local magnetoresistance effect in n-Ge devices with low-resistive Schottky-tunnel contacts. Applied Physics Express, 2019, 12, 033002.	2.4	11
110	Magnetoresistance of manganite thin films induced by reaction with substrate. Journal of Applied Physics, 2001, 89, 6320-6323.	2.5	10
111	Dynamic nuclear polarization induced by breakdown of fractional quantum Hall effect. Physical Review B, 2009, 79, .	3.2	10
112	Room-Temperature Tunneling Magnetoresistance in Magnetic Tunnel Junctions with a D0₃-Fe₃Si Electrode. Japanese Journal of Applied Physics, 2013, 52, 04CM02.	1.5	10
113	Formation of Ge(111) on Insulator by Ge epitaxy on Si(111) and layer transfer. Thin Solid Films, 2014, 557, 76-79.	1.8	10
114	Effect of annealing on the structure and magnetic properties of Co2FeAl0.5Si0.5 thin films on Ge(111). Journal of Alloys and Compounds, 2018, 748, 323-327.	5.5	10
115	Great Differences between Low-Temperature Grown Co₂FeSi and Co₂MnSi Films on Single-Crystalline Oxides. ACS Applied Electronic Materials, 2019, 1, 2371-2379.	4.3	10
116	Hanle spin precession in a two-terminal lateral spin valve. Applied Physics Letters, 2019, 114, 242401.	3.3	10
117	Electric field tunable anisotropic magnetoresistance effect in an epitaxial <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Co</mml:mi><mml:mn>2</mml:mn></mml:mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> interfacial multiferroic system. Physical Review Materials, 2021, 5, .	2.4	10
118	Control of magnetic anisotropy and magnetotransport in epitaxial micropatterned (Ga,Mn)As wire structures. IEEE Transactions on Magnetics, 2003, 39, 2785-2787.	2.1	9
119	The antiphase boundary in half-metallic Heusler alloy Co2Fe(Al,Si): atomic structure, spin polarization reversal, and domain wall effects. Applied Physics Letters, 2016, 109, .	3.3	9
120	Influence of the Ge diffusion on the magnetic and structural properties in Fe3Si and CoFe epilayers grown on Ge. Journal of Crystal Growth, 2017, 468, 676-679.	1.5	9
121	Effect of Feâ€“V nonstoichiometry on electrical and thermoelectric properties of Fe₂VAl films. Japanese Journal of Applied Physics, 2018, 57, 040306.	1.5	9
122	Critical thickness of strained Si_{1-x}Ge_x on Ge(111) and Ge-on-Si(111). Applied Physics Express, 2019, 12, 081005.	2.4	9
123	Experimental verification of the origin of positive linear magnetoresistance in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>CoFe</mml:mi><mml:mo>(</mml:mo><mml:msub><mml:mrow><m Heusler alloys. Physical Review B, 2019, 100, .	3.2	9
124	Direct observation of pseudo-gap electronic structure in the Heusler-type Fe2VAl thin film. Journal of Electron Spectroscopy and Related Phenomena, 2019, 232, 1-4.	1.7	9
125	Giant magnetoelectric effect in an L21-ordered Co2FeSi/Pb(Mg1/3Nb2/3)O3-PbTiO3 multiferroic heterostructure. Applied Physics Letters, 2021, 118, .	3.3	9
126	Sign determination of spin polarization in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>L</mml:mi><mml:msub><mml:mn>2</mml:mn><mml:mn>1</mml:mn></mml:msub></mml:mr xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="bold">Co</mml:mi><mml:mn mathvariant="bold">2</mml:mn></mml:msub><mml:mi mathvariant="bold">FeSi</mml:mi></mml:mrow></mml:math>using a Pt-based spin Hall device. Physical	3.2	8

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127	Low-temperature<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>B</mml:mi><mml:mn>2</mml:mn></mml:mrow></mml:math> and magnetic properties of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Fe</mml:mi><mml:mrow><mml:mn>100</mml:mn> on bcc alloys. Physical Review B, 2015, 92, .	3.2	8
128	Electrical properties of epitaxial Lu- or Y-doped La 2 O 3 /La 2 O 3 /Ge high- k gate-stacks. Materials Science in Semiconductor Processing, 2017, 70, 260-264.	4.0	8
129	Crack formation in strained SiGe grown on Ge-on-Si (111) and its suppression by patterning substrates. Materials Science in Semiconductor Processing, 2020, 117, 105153.	4.0	8
130	Half-metallic nature of the low-temperature grown Co2MnSi films on SrTiO3. Journal of Alloys and Compounds, 2021, 854, 155571.	5.5	8
131	Magnetoresistance ratio of more than 1% at room temperature in germanium vertical spin-valve devices with Co2FeSi. Applied Physics Letters, 2021, 119, .	3.3	8
132	Effect of Ga+ irradiation on magnetic and magnetotransport properties in (Ga,Mn)As epilayers. Journal of Applied Physics, 2005, 97, 10D302.	2.5	7
133	A magnetic tunnel junction with an L21-ordered Co2FeSi electrode formed by all room-temperature fabrication processes. Thin Solid Films, 2014, 557, 386-389.	1.8	7
134	Spin-dependent edge-channel transport in aSiâ•SiGequantum Hall system. Physical Review B, 2006, 73, .	3.2	6
135	Effect of the shape anisotropy on the magnetic configuration of (Ga,Mn)As and its evolution with temperature. Journal of Applied Physics, 2006, 99, 123901.	2.5	6
136	Dynamic Nuclear Polarization in a Quantum Hall Corbino Disk. Journal of the Physical Society of Japan, 2008, 77, 023710.	1.6	6
137	Ion channeling study of epitaxy of iron based Heusler alloy films on Ge(111). Thin Solid Films, 2011, 519, 8461-8467.	1.8	6
138	Effect of the magnetic domain structure in the ferromagnetic contact on spin accumulation in silicon. Applied Physics Letters, 2012, 101, 232404.	3.3	6
139	Room-temperature electrical creation of spin accumulation in n-Ge using highly resistive Fe3Si/n+-Ge Schottky-tunnel contacts. Thin Solid Films, 2014, 557, 382-385.	1.8	6
140	Effect of atomic-arrangement matching on La2O3/Ge heterostructures for epitaxial high-k-gate-stacks. Journal of Applied Physics, 2015, 118, .	2.5	6
141	Ion Irradiation Control of Ferromagnetism in (Ga,Mn)As. Japanese Journal of Applied Physics, 2005, 44, L816-L818.	1.5	5
142	Estimation of Electrically-Pumped Dynamic Nuclear Polarization in a Quantum Hall Device Using Tilted Magnetic Fields. Japanese Journal of Applied Physics, 2006, 45, L522-L524.	1.5	5
143	Effect of post annealing on hole mobility of pseudo-single-crystalline germanium films on glass substrates. Materials Science in Semiconductor Processing, 2017, 70, 68-72.	4.0	5
144	Epitaxial growth of Sb-doped Ge layers on ferromagnetic Fe₃Si for vertical semiconductor spintronic devices. Semiconductor Science and Technology, 2018, 33, 104008.	2.0	5

#	Article	IF	Citations
145	Proximity exchange coupling in a Fe/MgO/Si tunnel contact detected by the inverted Hanle effect. Physical Review B, 2019, 100, .	3.2	5
146	Control of thermoelectric properties in Mn-substituted <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Fe</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi>Vs</mml:mi><mml:mn></mml:mn></mml:r epilayers. Physical Review B, 2020, 102, .	3.2	5
147	Enhancement of the Spin Hall Angle by Interdiffusion of Atoms in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi>Co</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mrow><mml:mi>Fe</ / n - <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inl. Physical Review Applied, 2020, 14, .	3.8	5
148	A drastic increase in critical thickness for strained SiGe by growth on mesa-patterned Ge-on-Si. Applied Physics Express, 2021, 14, 025502.	2.4	5
149	Effect of Fe atomic layers at the ferromagnetâ€“semiconductor interface on temperature-dependent spin transport in semiconductors. Journal of Applied Physics, 2021, 129, .	2.5	5
150	Dynamic nuclear polarization and Knight shift measurements in a breakdown regime of integer quantum Hall effect. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1389-1391.	2.7	4
151	Effect of an Atomically Matched Structure on Fermi-level Pinning at Metal/p-Ge Interfaces. ECS Transactions, 2013, 50, 223-229.	0.5	4
152	An All-Epitaxial Fe₃Si/FeSi/Co₂FeSi Trilayer Grown by Room-Temperature Molecular Beam Epitaxy. IEEE Transactions on Magnetics, 2014, 50, 1-3.	2.1	4
153	Exchange coupling in metallic multilayers with a top FeRh layer. AIP Advances, 2016, 6, .	1.3	4
154	Magnetic properties and interfacial characteristics of all-epitaxial Heusler-compound stacking structures. Physical Review B, 2016, 94, .	3.2	4
155	Spin transport in antimony-doped germanium detected using vertical spin-valve structures. Applied Physics Express, 2020, 13, 023001.	2.4	4
156	Experimental extraction of donor-driven spin relaxation in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math> -type nondegenerate germanium. Physical Review B, 2021, 104, .	3.2	4
157	Anisotropic Magnetotransport due to Uniaxial Magnetic Anisotropy in (Ga,Mn)As Wires. IEEE Transactions on Magnetics, 2004, 40, 2682-2684.	2.1	3
158	Magnetization reversal with domain-wall pinning in (Ga, Mn)As wire. IEEE Transactions on Magnetics, 2005, 41, 2742-2744.	2.1	3
159	Spin-dependent nonlocal resistance in aSiâˆ•SiGequantum Hall conductor. Physical Review B, 2007, 75, .	3.2	3
160	Controlling the half-metallicity of Heusler/Si(1â€‰1â€‰1) interfaces by a monolayer of Siâ€“Coâ€“Si. Journal of Physics Condensed Matter, 2016, 28, 395003.	1.8	3
161	A low-temperature fabricated gate-stack structure for Ge-based MOSFET with ferromagnetic epitaxial Heusler-alloy/Ge electrodes. Japanese Journal of Applied Physics, 2016, 55, 063001.	1.5	3
162	Magnetic and structural depth profiles of Heusler alloy Co₂FeAl_{0.5}Si_{0.5} epitaxial films on Si(1â€‰1â€‰1). Journal of Physics Condensed Matter, 2018, 30, 065801.	1.8	3

#	Article	IF	Citations
163	Germanium pn junctions between ferromagnetic CoFe and Fe3Si layers for spintronic applications. Materials Science in Semiconductor Processing, 2020, 116, 105066.	4.0	3
164	Electrical Detection of Spin Transport in Si Using High-quality Fe3Si/Si Schottky Tunnel Contacts. Journal of the Magnetics Society of Japan, 2010, 34, 316-322.	0.9	3
165	Substrate dependent reduction of Gilbert damping in annealed Heusler alloy thin films grown on group IV semiconductors. Applied Physics Letters, 2021, 119, .	3.3	3
166	Superimposed contributions to two-terminal and nonlocal spin signals in lateral spin-transport devices. Physical Review B, 2021, 104, .	3.2	3
167	Converse Magnetoelectric Effect in Epitaxial Coâ„MnSi/Pb(Mg_{1/3}Nb_{2/3})Oâ„-PbTiOâ„ Multiferroic Heterostructures. IEEE Transactions on Magnetics, 2022, 58, 1-5.	2.1	3
168	Correlation between ferromagnetism and hole localization in very thin (Ga,Mn)As epilayers. Journal of Applied Physics, 2005, 97, 10D301.	2.5	2
169	Robust spin-current injection in lateral spin valves with two-terminal Co2FeSi spin injectors. AIP Advances, 2017, 7, 055808.	1.3	2
170	Inverse local magnetoresistance effect up to room temperature in ferromagnet-semiconductor lateral spin-valve devices. Materials Science in Semiconductor Processing, 2020, 113, 105046.	4.0	2
171	Increased Critical Thickness for Strained SiGe on Ge-on-Si(111). ECS Transactions, 2020, 98, 499-503.	0.5	2
172	Mechanism of crack formation in strained SiGe(1 1 1) layers. Journal of Crystal Growth, 2022, 589, 126672.	1.5	2
173	Structural insight using anomalous XRD into Mn2CoAl Heusler alloy films grown by magnetron sputtering, IBAS, and MBE techniques. Acta Materialia, 2022, 235, 118063.	7.9	2
174	Strong room-temperature EL emission from Ge-on-Si (111) diodes. Journal of Crystal Growth, 2022, , 126766.	1.5	2
175	Anomalous Hall resistivity due to grain boundary in manganite thin films. Journal of Applied Physics, 2003, 93, 8107-8109.	2.5	1
176	Spin selective transport at the ferromagnetic wire/GaAs interface. Journal of Magnetism and Magnetic Materials, 2005, 286, 103-107.	2.3	1
177	Magnetization Reversal by Electrical Spin Injection in Ferromagnetic (Ga,Mn)As-Based Magnetic Tunnel Junctions. Journal of Superconductivity and Novel Magnetism, 2005, 18, 3-7.	0.5	1
178	Gate-controlled nuclear magnetic resonance in an AlGaAsâ•GaAs quantum Hall device. Applied Physics Letters, 2006, 89, 202111.	3.3	1
179	Out-of-plane magnetization reversal processes of (Ga,Mn)As with two different hole concentrations. Journal of Applied Physics, 2006, 99, 093903.	2.5	1
180	High-quality ferromagnetic CoFe/Si contacts for Si spin-transistor applications. , 2010, , .		1

#	Article	IF	Citations
181	Generation and Detection of a Pure Spin Current Using Co-Based Heusler-Alloy Spin Injector and Detector: Comparison of Co2MnSi and Co2FeSi. ECS Transactions, 2013, 50, 245-251.	0.5	1
182	Spin Absorption Effect at Ferromagnet/Ge Schottky-Tunnel Contacts. Materials, 2018, 11, 150.	2.9	1
183	Modulation of magnetization dynamics in an epitaxial Heusler ferromagnet due to pure spin current in a laterally configured structure. Journal of Physics Condensed Matter, 2018, 30, 255802.	1.8	1
184	Magnetic and Transport Properties of Co1+<italic>x</italic>FeV1â^'<italic>x</italic>Si Epitaxial Films Grown by Molecular Beam Epitaxy. IEEE Transactions on Magnetics, 2019, 55, 1-4.	2.1	1
185	Crystal orientation effect on spin injection/detection efficiency in Si lateral spin-valve devices. Journal Physics D: Applied Physics, 2019, 52, 085102.	2.8	1
186	Study of Spin Transport and Magnetoresistance Effect in Silicon-based Lateral Spin Devices for Spin-MOSFET Applications. Journal of the Magnetics Society of Japan, 2020, 44, 56-63.	0.9	1
187	Growth of ferromagnetic Co2FeSi films on flexible Ge(111). Materials Science in Semiconductor Processing, 2020, 112, 104997.	4.0	1
188	Experimental estimation of the spin diffusion length in undoped p-Ge on Fe3Si using vertical spin-valve devices. Journal of Applied Physics, 2021, 129, 013901.	2.5	1
189	Spin signals in Si non-local transport devices with giant spin accumulation. , 2017, , .		1
190	MÃ¶ssbauer Analysis. Springer Series in Materials Science, 2016, , 341-352.	0.6	1
191	Proximity exchange coupling across an MgO tunnel barrier detected via spin precession. , 2020, , .		1
192	(Invited) Strain Engineering of Si/Ge Heterostructures on Ge-on-Si Platform. ECS Transactions, 2020, 98, 267-276.	0.5	1
193	Temperature Dependence of Two-Terminal Local Magnetoresistance in Co-Based Heusler Alloy/Ge Lateral Spin-Valve Devices. IEEE Transactions on Magnetics, 2022, 58, 1-5.	2.1	1
194	Control of magnetic features in epitaxial micro-patterned (Ga,Mn)As wire structures. , 0, , .		0
195	Magnetotransport measurement of (Ga,Mn)As epilayers with low-temperature annealing. Electrochimica Acta, 2005, 51, 1004-1007.	5.2	0
196	Magnetization reversal with domain-wall pinning in (Ga,Mn)As wires. , 2005, , .		0
197	Spin dependence of edge-channel transport in silicon- based quantum Hall systems. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4251-4254.	0.8	0
198	Estimation of dynamic nuclear polarization in quantum-Hall devices using tilted magnetic fields. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4384-4387.	0.8	0

#	Article	IF	Citations
199	Local detection of Knight shift around quantum-Hall edge channels using resistively-detected NMR. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4368-4371.	0.8	0
200	SPATIAL DISTRIBUTION OF KNIGHT SHIFT AROUND QUANTUM HALL EDGE CHANNELS USING RESISTIVELY-DETECTED NMR. International Journal of Modern Physics B, 2007, 21, 1440-1444.	2.0	0
201	Valley-splitting edge-channel transport in a Si/SiGe quantum Hall system. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1523-1525.	2.7	0
202	Atomically-controlled Fe<inf>3</inf>Si/Ge hybrid structures for group-IV-semiconductor spin-transistor application. , 2008, , .		0
203	Low Temperature Epitaxial Growth of Full Heusler Alloy Fe₂MnSi on Ge(111) Substrates for Spintronics Application. ECS Transactions, 2008, 16, 273-276.	0.5	0
204	Ferromagnetic Co<inf>3−x</inf>Fe<inf>x</inf>Si/Si(111) contacts with high-quality heterointerfaces for spin-transistor applications. , 2010, , .		0
205	Formation of ultra-shallow Ohmic contacts on n-Ge by Sb delta-doping. Materials Research Society Symposia Proceedings, 2011, 1305, 1.	0.1	0
206	(Invited) SiGe Spintronics with Single-Crystalline Ferromagnetic Schottky-Tunnel Contacts. ECS Transactions, 2013, 50, 235-243.	0.5	0
207	Ion beam analysis of quaternary Heusler alloy Co₂(Mn_{1â€“x}Fe_x)Si(111) epitaxially grown on Ge(111). Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1828-1831.	0.8	0
208	Effect of Sn-doped Ge insertion layers on epitaxial growth of ferromagnetic Fe<inf>3</inf>Si films on a flexible substrate. , 2014, , .		0
209	Low-temperature Grown Ge<inf>1−x</inf>Sn<inf>x</inf> layers on a metallic silicide. , 2014, , .		0
210	Atomically controlled heteroepitaxy of Ge on a ferromagnetic heusler alloy for a vertical-type spin transistor. , 2014, , .		0
211	Atomic and electronic structure study of a Co 2 FeAl 0.5 Si 0.5 half-metal thin film on Si(111). Microscopy and Microanalysis, 2016, 22, 1524-1525.	0.4	0
212	(Invited) Finely Controlled Heterointerfaces between Ge(111) and Metallic Alloys or Insulators for Next Generation Ge-Based Devices. ECS Transactions, 2016, 75, 651-659.	0.5	0
213	Atomic study of Hybrid Spintronic Heterostructures: Co2FeAl05Si0.5/Ge(111). Microscopy and Microanalysis, 2017, 23, 1762-1763.	0.4	0
214	Large local magnetoresistance at room temperature in Si<100> devices. , 2018, , .		0
215	Significant effect of interfacial spin moments in ferromagnet-semiconductor heterojunctions on spin transport in a semiconductor. Physical Review B, 2022, 105, .	3.2	0
216	Epitaxial Mn<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si86.svg" display="inline" id="d1e594"><mml:msub><mml:mrow /><mml:mrow><mml:mn>2</mml:mn></mml:mrow></mml:msub></mml:math>VAl films with <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si85.svg" display="inline" id="d1e602"><mml:mrow><mml:mi>L</mml:mi><mml:msub><mml:mrow><mml:mn>2</mml:mn></mml:mrow><mml:mrow><mml:mn> structure for all-Heusler stacks. Journal of Magnetism and Magnetic Materials, 2022, , 169644.	2.3	0